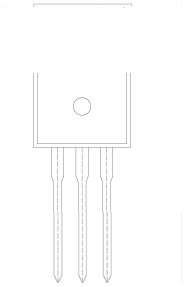
TO-220S Ultrafast Recovery Diode in a TO-220S Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.



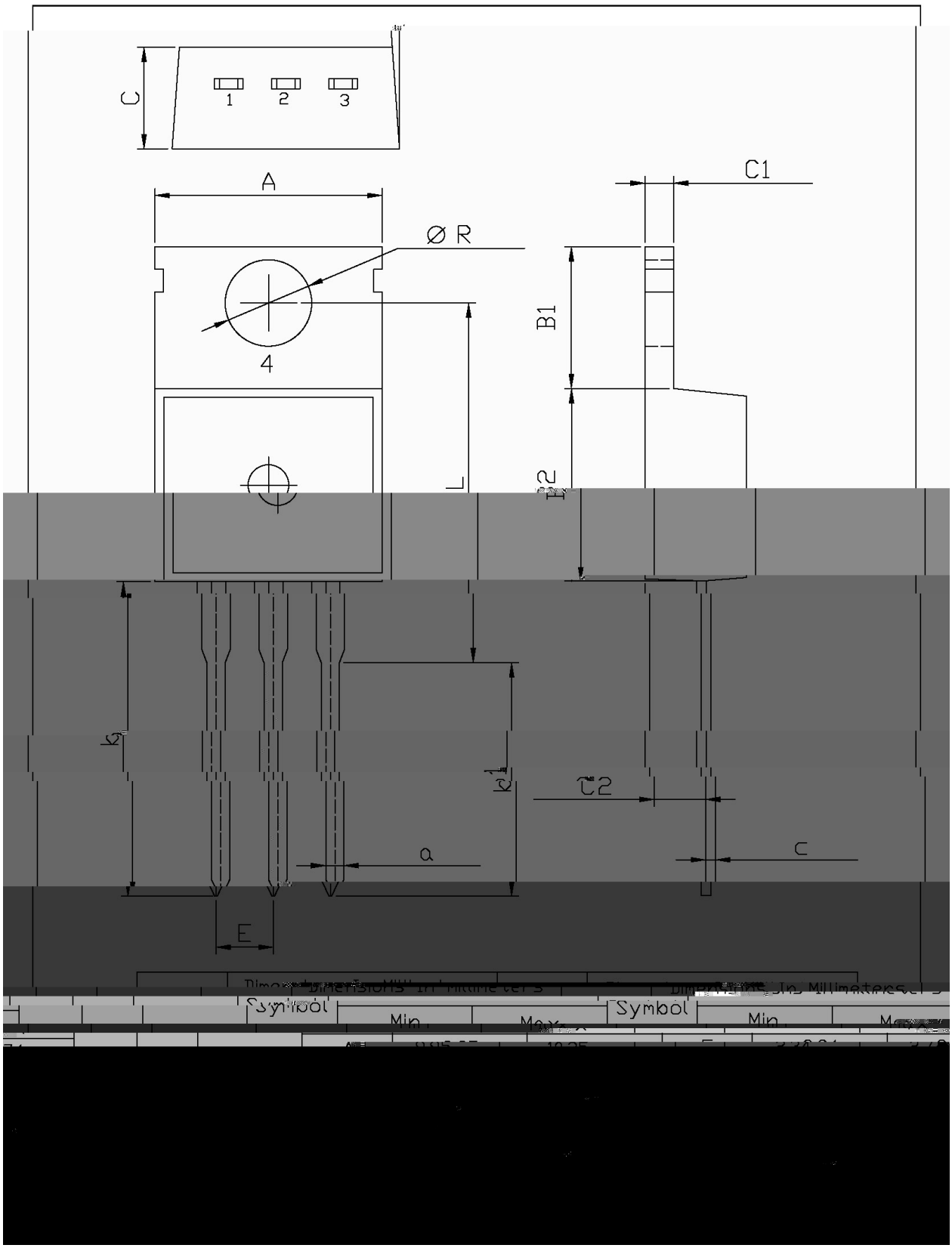
PIN1 Anode PIN 2 Cathode PIN 3 Anode PIN 4 NC

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Rectified Forward Current	I_F	2×8	A
Non Repetitive Peak Surge Current	I_{FSM}	120	A
Thermal Resistance Junction to Case	R_{Jc}	2.9	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Forward Voltage	V_F	I_F=2A	Tc=25		0.80		V
		I_F=2A	Tc=125		0.66		V
		I_F=8A	Tc=25		0.93	1	V
		I_F=8A	Tc=125		0.82	0.9	V
Instantaneous Reverse Current	I_R Note 1						

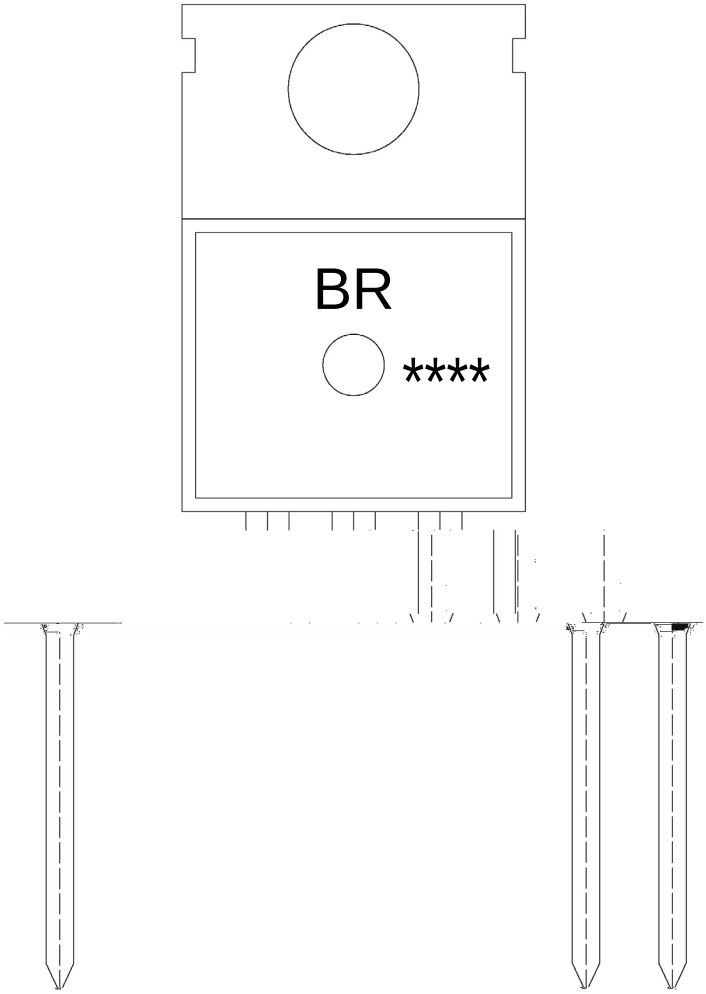
/ Package Dimensions

TO-220S Unit: mm



Symbol	Min	Max	Symbol	Min	Max

/ Marking Instructions



BR

MURJ1620

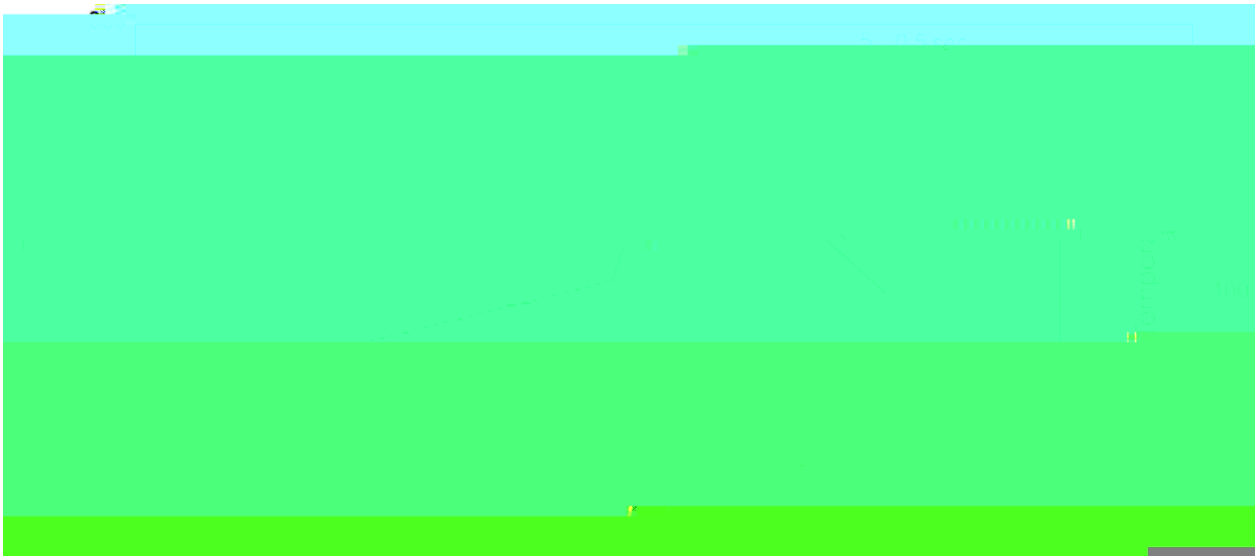
CT:

****

Note:

BR:	Company Code
MURJ1620	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



					Note:
1	25	150	60	90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5			5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type	Units					Dimension (unit mm^3)		
	Units/Tube /	Tubes/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Tube	Inner Box	Outer Box
TO-220S	50	20	1000	5	5000	532×31.4×5.5	555×164×50	575×290×180

/ Notices